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# 2SD467

Silicon NPN Epitaxial

# HITACHI

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## Application

- Low frequency power amplifier
- Complementary pair with 2SB561

## Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

**Absolute Maximum Ratings** (Ta = 25°C)

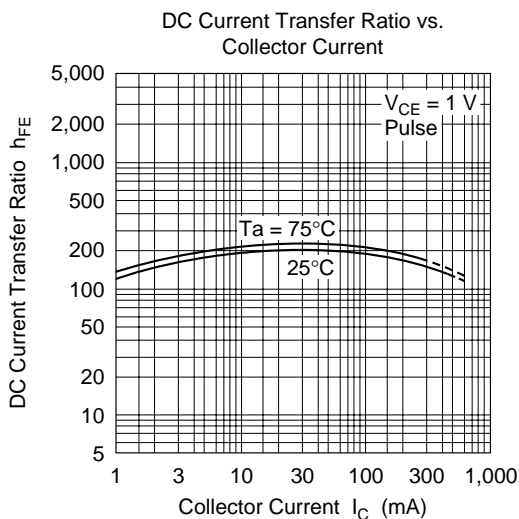
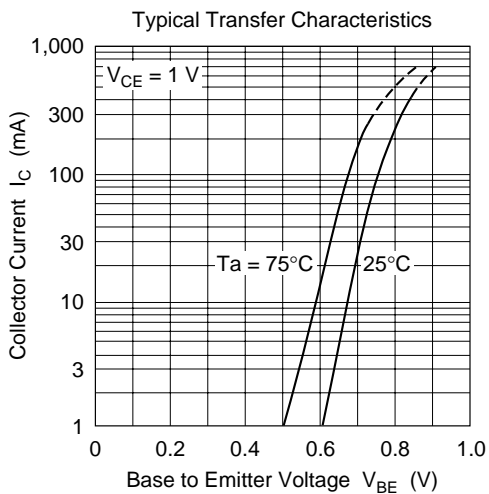
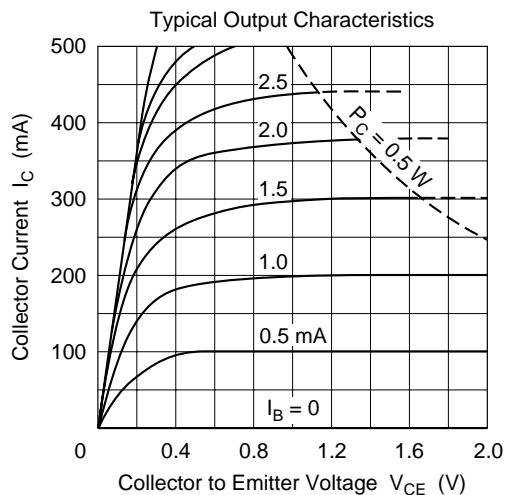
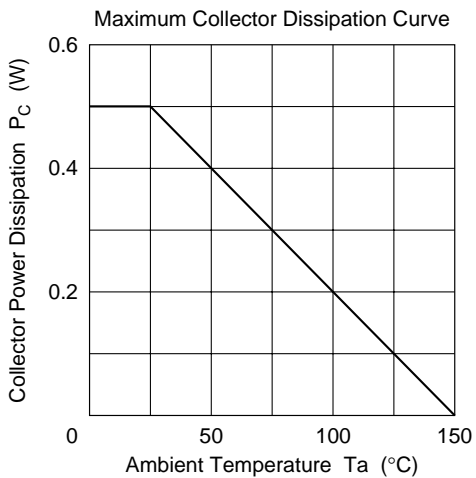
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	25	V
Collector to emitter voltage	$V_{CEO}$	20	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	0.7	A
Collector peak current	$i_{C(peak)}$	1.0	A
Collector power dissipation	$P_C$	0.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

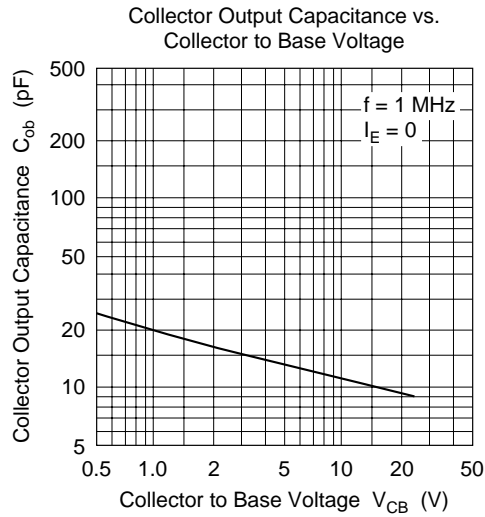
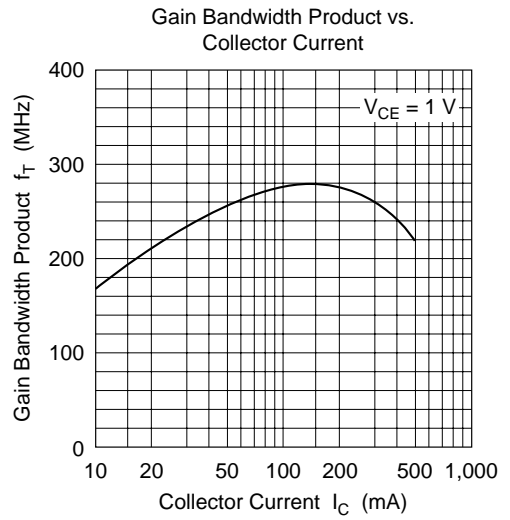
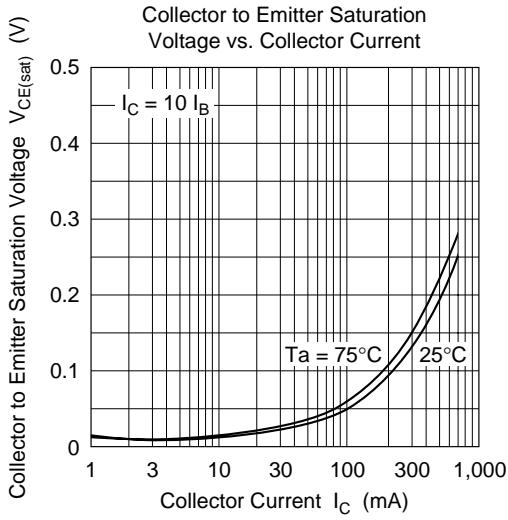
**Electrical Characteristics** (Ta = 25°C)

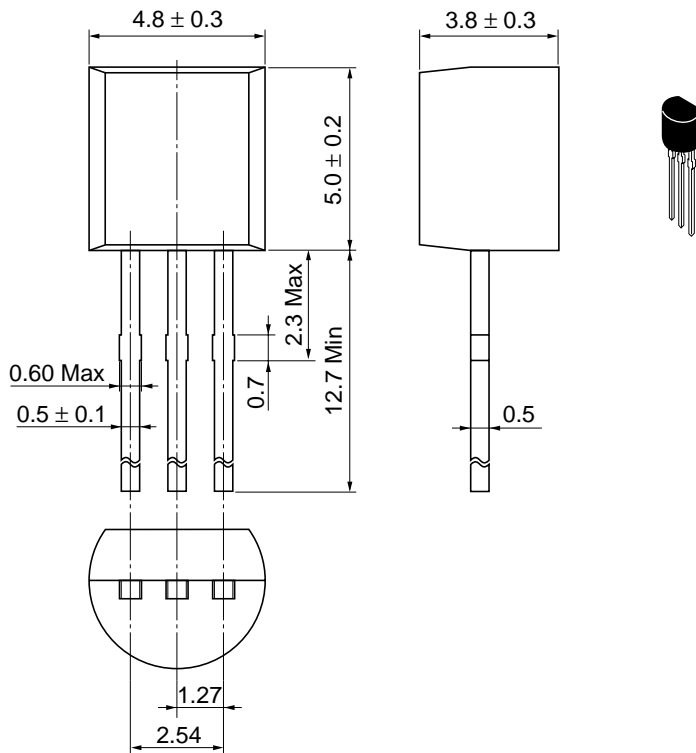
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	—	—	V	$I_C = 1 mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	1.0	$\mu A$	$V_{CB} = 20 V, I_E = 0$
DC current transfer ratio	$h_{FE}^{*1}$	85	—	240		$V_{CE} = 1 V, I_C = 0.15 A$ (Pulse test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.19	0.5	V	$I_C = 0.5 A, I_B = 0.05 A$ (Pulse test)
Base to emitter voltage	$V_{BE}$	—	0.76	1.0	V	$V_{CE} = 1 V, I_C = 0.15 A$ (Pulse test)
Gain bandwidth product	$f_T$	—	280	—	MHz	$V_{CE} = 1 V, I_C = 0.15 A$ (Pulse test)
Collector output capacitance	Cob	—	12	—	pF	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$

Note: 1. The 2SD467 is grouped by  $h_{FE}$  as follows.

B	C
85 to 170	120 to 240







Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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